# Electronic Supplementary Information

A fast room-temperature strategy for direct reduction of graphene oxide films towards flexible transparent conductive films

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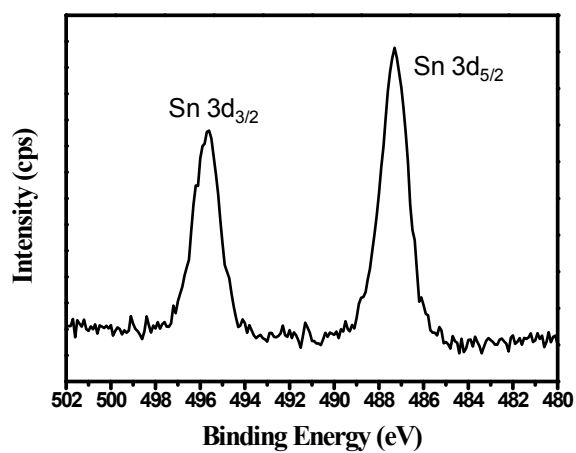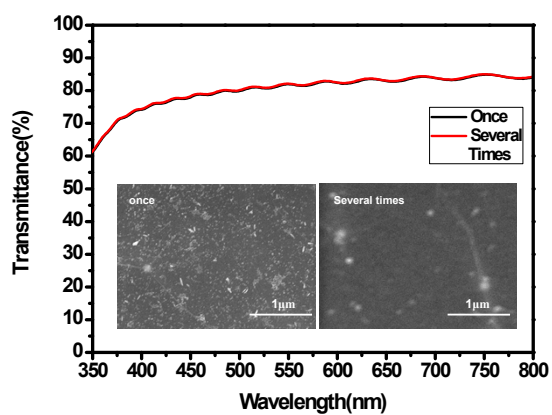[b] University of Chinese Academy of Sciences, Beijing 100039, China
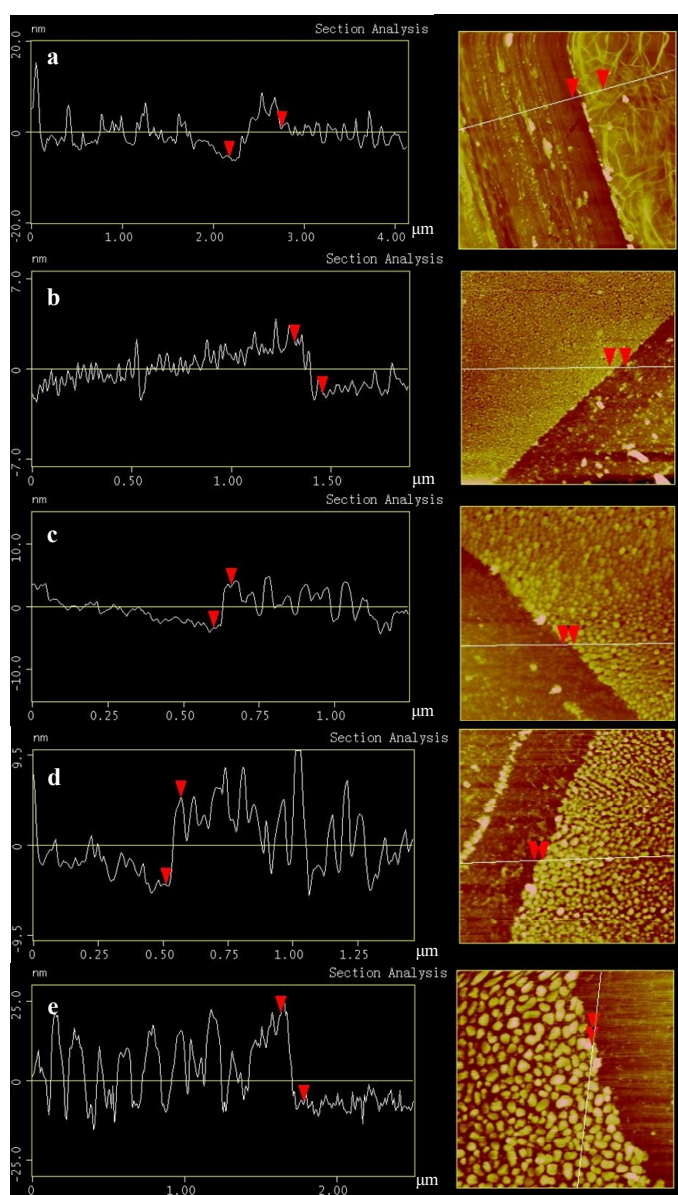
Figure S1. The AFM image of a) the GO film of 6.3nm, and b-e) the as-sputtered Sn nanoparticle layer of different thicknesses.
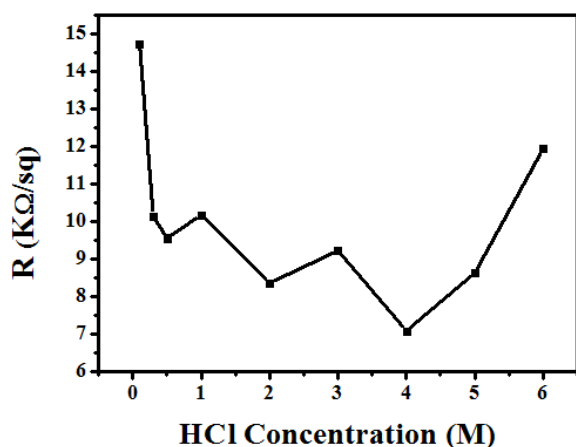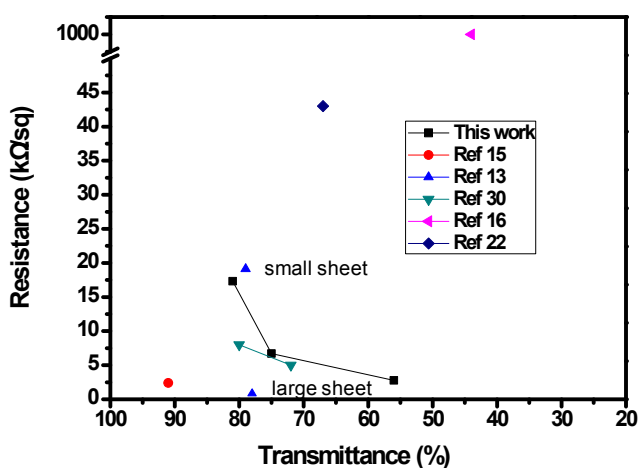
Figure S2. The influence of the concentration of the HCl solution to the conductivity of the rGO film.

Figure S3. Magnified XPS spectrum of Sn 3d in Sn-RGO sample.

Figure S4. The change of morphology and transmittance before and after constantly washing the film.

Figure S5. Comparison of the conductivity and transparency between the as prepared Sn-rGO and the rGO films fabricated in other methods on flexible substrates.

Sample	XPS*	XRD	Raman	TGA
	C/O ratios	d spacing (nm)	I_D/I_G	Total weight loss (%)
GO	3.1	0.773	0.9	60
Ref 24 (Zn)	21.2		1.22	3
Ref 25 (Fe)	2.6~7.9		0.32~1.02	7~34
Ref 29 (Al)	18.6	0.375	1.81	
Ref 23	6.67	0.362	1.10	12.05
Sn-rGO	17.2	0.373	1.14	15

Table S1. Comparison of the property results of the as prepared Sn-rGO film and that from other different reducing methods (mainly metal reduction).